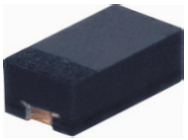
SMD Schottky Barrier Diode

CDBU0140L

Io = 100 mA
VR = 40 Volts
RoHS Device



Features

-Low forward voltage.

-Designed for mounting on small surface.

-Extremely thin / leadless package.

-Majority carrier conduction.

Mechanical data

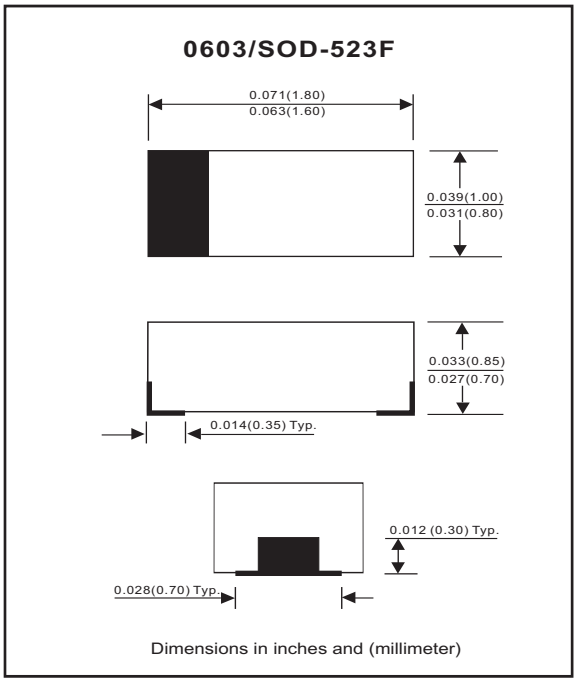
-Case: 0603/SOD-523F standard package, molded plastic.

-Terminals: Gold plated, solderable per MIL-STD-750,method 2026.

-Polarity: Indicated by cathode band.

-Mounting position: Any

-Weight: 0.003 gram(approx.).



Maximum Rating (at TA=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Repetitive Peak reverse voltage		VRRM			45	V
Reverse voltage		VR			40	V
Average forward rectified current		IO			100	mA
Forward current,surge peak	8.3 ms single half sine-wave superimposed on rate load (JEDEC method)	IFSM			1	A
Storage temperature		TSTG	-40		+125	°C
Junction temperature		Tj			+125	°C

Electrical Characteristics (at TA=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	IF = 100mA IF = 10mA	VF			0.55 0.34	V
Reverse current	VR = 10V	IR			30	uA
Capacitance between terminals	f = 1 MHz, and 10 VDC reverse voltage	CT		6		pF

RATING AND CHARACTERISTIC CURVES (CDBU0140L)

Fig. 1 - Forward characteristics

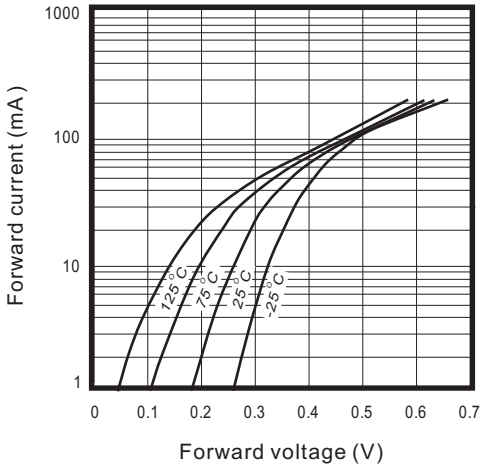


Fig. 2 - Reverse characteristics

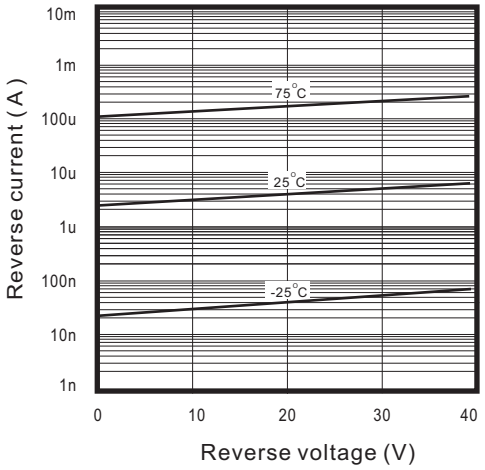


Fig. 3 - Capacitance between terminals characteristics

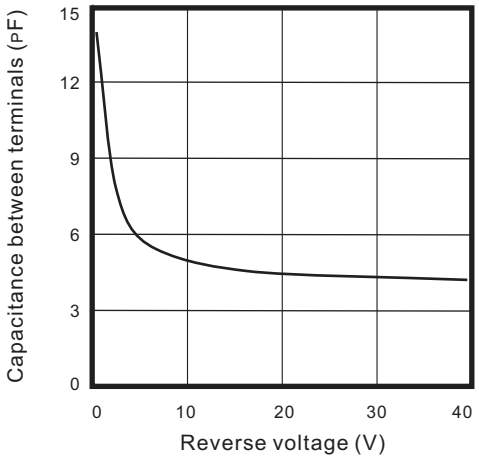


Fig.4 - Current derating curve

